[redacted]

SEARCHED

Class	Sub.	Date	Exmr.
174	250	1/22/02	GNV
	260		
	261		
	267		
Update	Search	9/17/02	TD
174	257-258		
	265		
	266		
216	27		
A38	734		
	750		

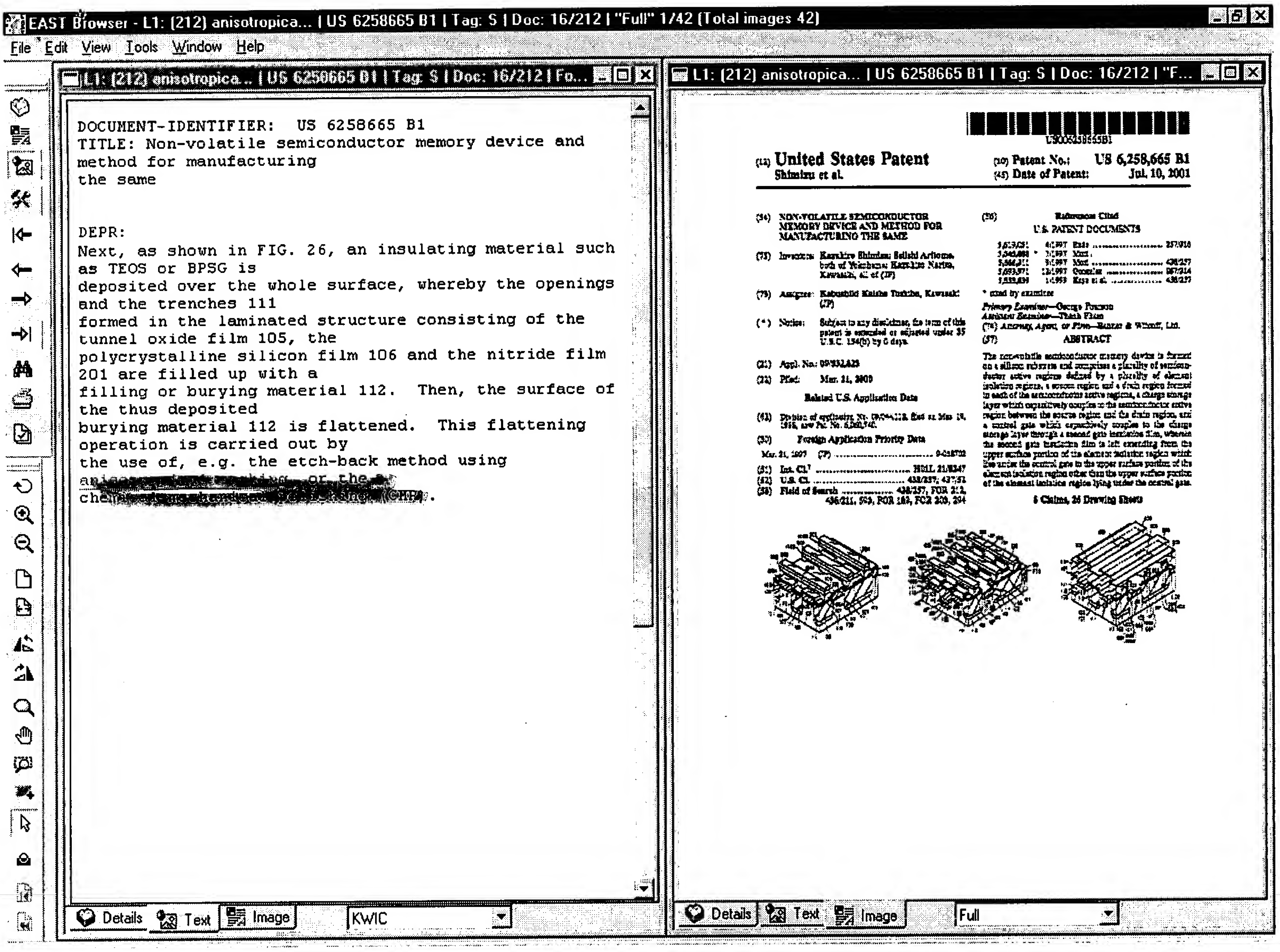
SEARCH NOTES
(INCLUDING SEARCH STRATEGY)

	Date	Exmr.
East search	1/22/02	GAV

INTERFERENCE SEARCHED

Class	Sub.	Date	Exmr.

(RIGHT OUTSIDE)



DOCUMENT-IDENTIFIER: US 6258665 B1
TITLE: Non-volatile semiconductor memory device and method for manufacturing the same

DEPR:
Next, as shown in FIG. 26, an insulating material such as TEOS or BPSG is deposited over the whole surface, whereby the openings and the trenches 111 formed in the laminated structure consisting of the tunnel oxide film 105, the polycrystalline silicon film 106 and the nitride film 201 are filled up with a filling or burying material 112. Then, the surface of the thus deposited burying material 112 is flattened. This flattening operation is carried out by the use of, e.g. the etch-back method using an [redacted].

(12) United States Patent
Shimizu et al.

(10) Patent No.: US 6,258,665 B1
(45) Date of Patent: Jul. 10, 2001

(54) NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR MANUFACTURING THE SAME

(56) References Cited
U.S. PATENT DOCUMENTS

(57) ABSTRACT